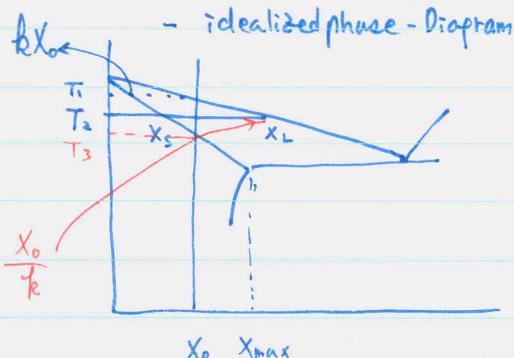


4.3 Alloy Solid'n.

a single-phasebinary, eutectic, peritectic.

1. Solid'n of Single-Phase Alloys.



$$k \text{ (partition coeff.)} = \frac{x_S}{x_L} - \text{mole frac. } < 1$$

Assume $k \neq f_{\text{ccomp.}}$

- a planar S-L interface assumed
file in a zone-melting. (simple).

- Three limiting cases.

1. slow (equil^m) solidif'n (full diff. in solid)
2. solidif'n w/o diffusion in the solid
perfect mixing in the liquid.
3. solidif'n w/o diffusion in the solid
diffusional mixing in the liquid.

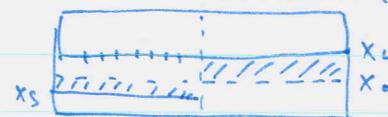
All one directional Solid'n

i) * Equil^m solidif'n.

*) slow cooling. sufficient time for diffusion in solid & liquid : $\therefore kx_0, x_0$

- the rel. amount of solid and liquid - lever rule.

slow enough from $T_1 \rightarrow T_3$



shaded area equal

x_S

x_L

x_0

kx_0

(a)

x_S

x_L

x_0

kx_0

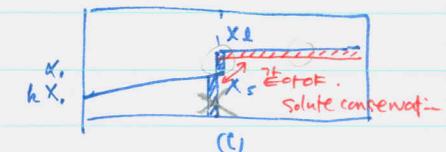
(b)

Fig. 4.20.

ii) * No diff. in solid, perfect Mixing in Liquid.

(*) cooling too rapid.

stirring



x_S

x_L

x_0

x_{max}

Fig. 4.21 (d)

$$c_{fs} + c_{fl} = C_0$$

weight fraction

(12)

Date . . .

- no diffusion in the solid, the separate layers of solid retain their original compositions. \rightarrow avg. comp. of the solid (\bar{X}_s) $< X_s$
- The rel. amount of s. & l. determined by the lever rule using " \bar{X}_s and X_L "

$X_L \xrightarrow[\text{equl.}]{\text{diffusion}} \bar{X}_s \approx X_s$ (after comp. $\approx X_s$)

- Liquid become richer than $X_E/k \rightarrow X_E$!! final eutectic stnre
 \rightarrow Fig 4.21(d) $\bar{X}_s = X_o / (k+1)$

- The variation of X_s : solute rejected to the liquid mass balance $(X_L - X_s) df_s = (1-f_s) dX_L$

- Integrate this eq. B.C. $X_s = k X_o$ when $f_s = 0$.

$$\int_0^{f_s} \frac{df_s}{1-f_s} = \int_{X_o}^{X_L} \frac{dX_L}{X_L - X_s} = \int \frac{dX_L}{X_L(1-k)}$$

$$\therefore \int_0^{f_s} (1-k)(-1) d \ln(1-f_s) = \int_{X_o}^{X_L} d \ln X_L$$

$$(4.33) \quad \rightarrow \quad \ln \frac{X_L}{X_o} = (k-1) \underbrace{\ln(1-f_s)}_{f_s} \quad \therefore X_L = X_o f_s^{(k-1)} \\ \text{non-equil. lever rule.} \\ (\text{Scheil Eq.)}$$

Scheil eq $\rightarrow k < 1 \therefore k-1 < 0 \rightarrow$ predicts that if no diff. in the solid some eutectic always exist to solidify. $X_L = \frac{X_o}{f_s^{1-k}}$ $\uparrow X_E$ \leftarrow 작다

iii) * No Diffusion in Solid, Diffusional Mixing in Liquid

Solute rejected from solid \rightarrow diffuse into liquid. w/ limitation.

\therefore rapid build up of solute in front of the solid

$\rightarrow \therefore$ rapid increase in the comp. of solid forming.

- initial transient

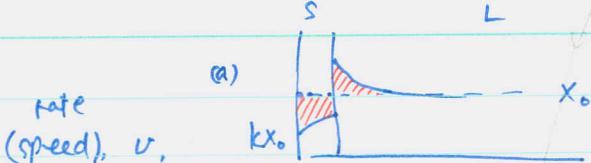
- If it solidifies at a const (speed), v ,

then a steady state is finally obtained at T_3 in Fig 4.19

- Liquid $\frac{x_0}{k}$, solid x_0 .

- Darcy s.state growth.

mass balance

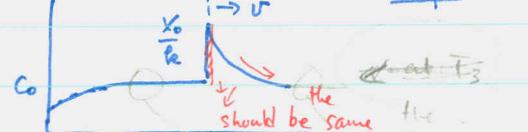


$$\text{rate} = kx_0$$



$$\text{reference } \delta \rightarrow v$$

$$x_0/k \rightarrow v$$



$$\text{at } T_3$$

Fig 4.22 at T_3

-(4.22)

$$\text{more precisely } D_L \frac{d^2 X_L}{dx^2} + v \frac{dX_L}{dx} = 0$$

how? 4.1!

$$(4.35) \quad - \text{Solution of this} \quad X_L = X_0 \left[1 + \frac{1-k}{k} \exp\left(-\frac{x}{(D/v)}\right) \right]$$

- Characteristic width $x = D/v \rightarrow \exp(-1) \rightarrow \frac{1}{e}$

$$x_L - x_0 = \left[\frac{1-k}{k} X_0 \right] e^{-1} \quad \text{max of } 30\%$$

- If the s-l interface is within $\sim D/v$ of the end of the bar \rightarrow compressed to final transient (eutectic comp)



→ In practice, have features from all three of the cases. i), ii), iii)

yes, stirring (pouring, convection current) but not sufficient

yes, some lig. diffusion betw Figs 4.21 d and 4.22 c

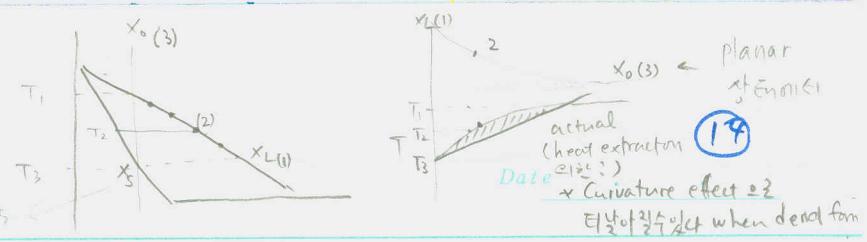
yes, diffusion in solid too, especially when interstitial atoms (solute)

and bcc (open space) solvent \rightarrow solute diffuse into liquid and solid, either way.

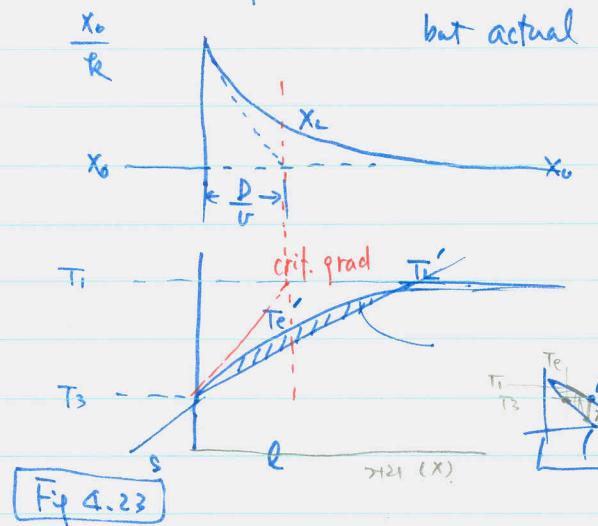
iv) Cellular and Dendritic Solidification.

solute diffus. ^{in alloy} similar to the conduct. of latent heat. in pure metal
possible to break up the planar front into dendrites.

→ complicated by possible temp. grad. in the liquid
(mixed problem ^① pure + alloy, instability)



- Varying solute conc. ahead of solid in front. \rightarrow Corresponding variation of equil^m
but actual temp. grad is T_L . Solid in temp. T_e



At the interface $T_3 = T_e = T_L$.

if the slope of crit. grad > that of T_L .

it is supercooled. \rightarrow Constitutional Supercooling
(due to comp.)

- A necessary condition for stable protrusions on a planar interface
 \rightarrow a region of constitutional supercooling even if $T_L' < T_e'$, temp at the tip of any protrusion $>$ that of surrounding
i.e., if $T_L' < T_e'$, protrusion develops. (dendritic or columnar)
 \leftarrow dendrite development.

If $T_L' > T_e'$.. melts. \rightarrow to dilute the liquid. (why: back!)

- S. state growth : The critical grad = $\frac{T_l - T_s}{(D/V)}$ T_l : liquidus, T_s : solidus.

① planar

$$\therefore T_L' = \frac{dT_L}{dx} > \frac{T_l - T_s}{D/V}$$

stable planar interface.

(4.36) Rearrange $T_L'/V > (T_l - T_s)/D$ for planar.

known as equil^m freezing range

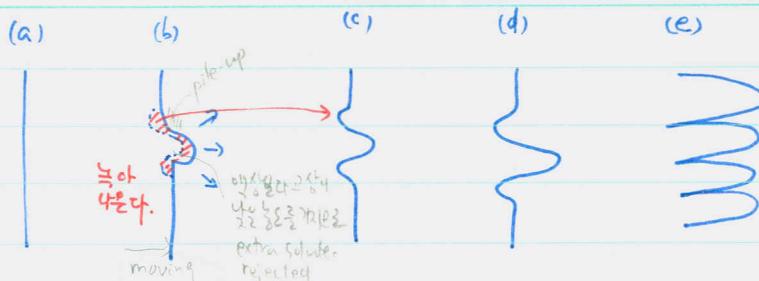
- Planar solid in difficult w/ large " " high V .

- $\frac{dT}{dx}$, or controlled by heat conduction.

② dendrite

- If $\frac{dT}{dx}$ in front of planar interface < the crit. grad. \rightarrow break down
of the planar \rightarrow forming a cellular structure

Fig. 4.24.



(b) the solutes rejected laterally piles up at the root of the protrusion.

(c) \hookrightarrow lowers T_e and \therefore results in recesses to form.

higher solute conc. of liquid
i.e., solute conc. \uparrow $T_e \downarrow$ but real temp. is higher than T_e
to be isothermal, need more "solvent" to dilute \rightarrow melting.

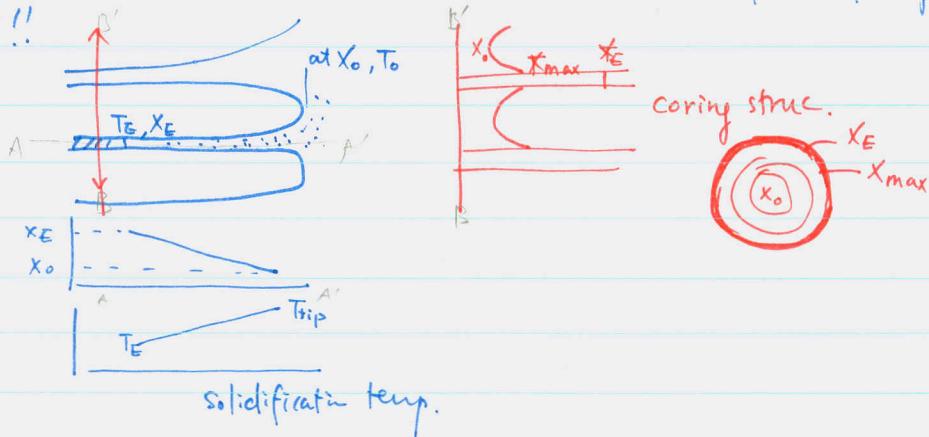
(d) this cause other protrusion.

(e) the same situation repeated (b) - (c), - (d) \rightarrow cellular struc.
as the s-l interface advances.

\rightarrow The solute rejected from the solidifying liquid remain bet'n cell walls.
solidifies last at T_e .

\rightarrow the tips of cellular struc. grow into the hottest liquid at X_o
how to solidify at high temp. (lowest conc.)

Fig. 4.25 !!



- Cellular struc. \rightarrow develops 2nd arm \rightarrow tertiary arms

\downarrow

dendritic struc.

stable only for at sufficiently low temp. at still lower temp.

a certain range of

grad.

grad.

서울대학교 공과대학 무기재료공학과

Department of Inorganic Materials Engineering

direct

or preferred X-tallography

- the direction of primary arm \rightarrow determined by the direc. of heat flow

c. supercool \downarrow $\frac{X_S}{X_L}$ column.

.. $\frac{X_S}{X_L}$ " dendritic growth

(16)



- tendency to form dendritic struc ↑ as the solidin range ↑

?? small partition ($k_2 = \frac{X_S}{X_L}$) \rightarrow dendritic conc.

large " ($k_2 \approx 1$) \rightarrow cellular ? effect of 2nd solutes

possibly related to the constitutional supercooling \rightarrow interface instability
(DS) in the transverse dir

- Directional Solidification : no temp. grad. perpendicular to the growth direct:

- why dendrites develop from cell? no clear.

Maybe in DS : that which reduces the constl supercooling to a very low level.

- observation consistent d. spacing ↓ as cooling rate ↑

higher cooling rate \rightarrow less chance for lateral diffusion of solute

\rightarrow required smaller cell. d.a. spacing to avoid c. supercooling

2. Eutectic Solidification

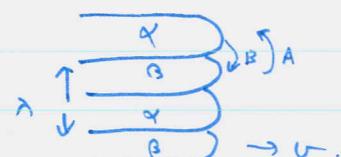
Quiz #2

- rxn $L \rightarrow \alpha + \beta$, classified - normal, anomalous eutectic rxns.

→ ① normal struc: two phases in the form of alternating lamellae
~~from~~ focus on this struc. \hookrightarrow grow simultaneously behind an planar S-l interf
 \hookrightarrow obtained when both phases have low ΔS_m

② Anomalous struc: occurs when one of the two phases is capable of faceting. high $\Delta S_m (= \frac{\Delta H_m}{T_m})$. \rightarrow flaky struc. in Al-Si

i) Growth of Lamellar Eutectic.



the rate of growth depends on

the diffusion of A, B. \rightarrow to α, β .

- small spacing (λ) \rightarrow rapid growth

- But small $\lambda \rightarrow$ increases the interfacial E, $\gamma_{\alpha\beta}$,
Should be balanced !!

(17)

Date . . .

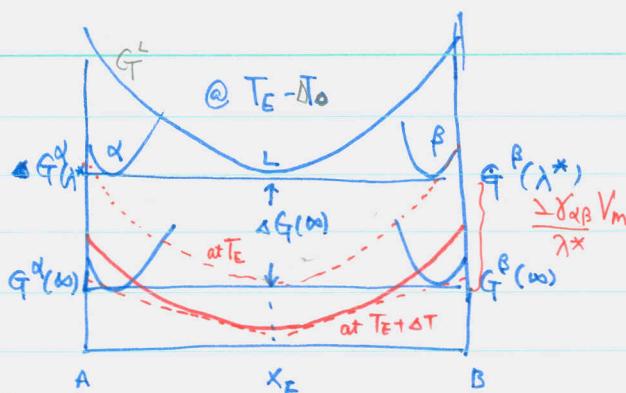


Fig 4.32

for λ , total area of α/β interface/m³
 $= (\frac{2}{\lambda}) \text{ m}^2/\text{m}^3$.

$$(4.37) \quad \Delta G(\lambda) = -\Delta G(\infty) + \frac{2}{\lambda} \gamma_{AB} V_m$$

for the solidification of 1 mole liquid.

↓ mean Vol.

(4.38) w/ ΔT_0 undercooling below T_E

$$\Delta G(\infty) \underset{\lambda \rightarrow \infty}{\approx} \frac{\Delta H \cdot \Delta T_0}{T_E}$$

$$\Delta G_\infty = \Delta H \cdot \frac{T_E}{T_E - \Delta T_0}$$

$$= \Delta H \cdot \frac{\Delta T_0}{T_E - \Delta T_0}$$

$$= \Delta H \cdot \frac{\Delta T_0}{T_E}$$

∴ min. $\lambda \rightarrow \lambda^*$ obtained when $\Delta G(\lambda^*) = 0$

$$(4.39) \quad \lambda^* = \frac{2 \gamma_{AB} V_m T_E}{\Delta H \cdot \Delta T_0}$$

and cutectic, i.e., at equil^m at λ^*

- α/β interface raises the $\Delta G^A(\lambda)$, $\Delta G^B(\lambda)$

∴ balance interfacial tension $\alpha/\beta/L$ triple pt.

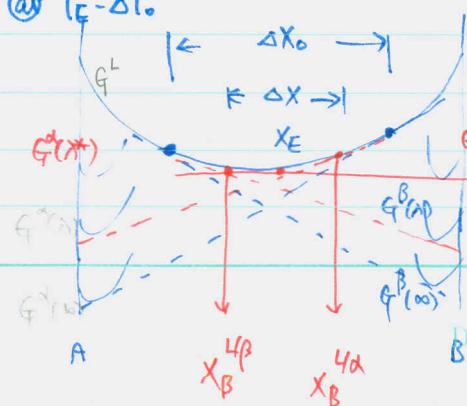
* Mechanism of Growth.

- for solidification to occur, need a flux of atoms between tips of α & β .

: conc. of B higher at the tip of α than those of β .



- If $\lambda = \lambda^*$ growth will be very slow. ∵ the lig. comp in contact w/ α, β is the same. ($= X_E$)

@ $T_E - \Delta T_0$ 

if $\lambda > \lambda^*$ less free E. is locked in the interfaces and G^A , G^B are reduced.

∴ the liquid in front of $\alpha = X_B^{4\alpha}$ (B-richer than $X_B^{4\beta}$) → diffusion → prem

$$\Delta G_V = \frac{2\delta V_m}{r} = \Delta G_F = \frac{L_v \Delta T_r}{T_m}$$

$$\therefore \Delta T_r = \frac{2\delta V_m}{r \cdot L_v}$$

(18)

* Mobility of the Interface

- the mobile interface (diffusion controlled). $v \propto J$ of solute $= -D \frac{dc}{dx}$
- I measured along the direction of diffusion. $\therefore \frac{dc}{dx}$ is not a single value

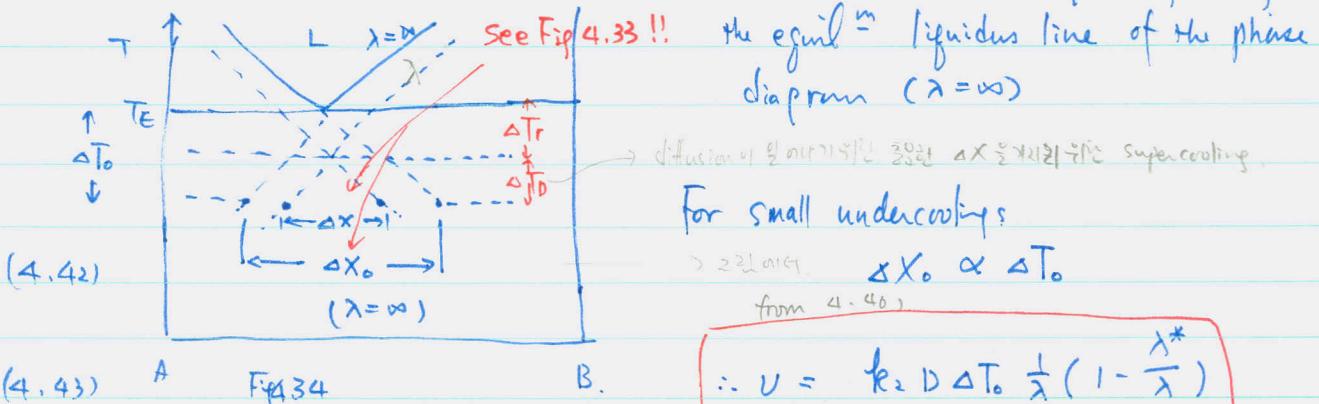
$$(4.40) \quad v = k_1 D \frac{\Delta x}{\lambda} \quad \text{when } \Delta x = X_B^{4\alpha} - X_B^{4\beta} = f(\lambda)$$

$$\Delta G(\lambda) = 0, \text{ equil}^m \rightarrow v = 0, \rightarrow \Delta x = 0.$$

- $\Delta x = 0$ when $\lambda = \lambda^*$, as $\lambda \uparrow \Delta x \rightarrow \Delta x_0$, max. value.

roughly \rightarrow this is true \rightarrow diff. L \rightarrow all at X_B

$$(4.41) \quad \Delta x = \Delta x_0 \left(1 - \frac{\lambda^*}{\lambda}\right) \quad \Delta x_0 \text{ can be obtained by extrapolating}$$



$$(4.43) \quad \therefore v = k_2 D \Delta T_0 \frac{1}{\lambda} \left(1 - \frac{\lambda^*}{\lambda}\right)$$

- (4.43) shows, by varying $\Delta T_0 \rightarrow$ vary v . λ , independently. Experiments shows a λ (always is) assisted w/ a v

- From (4.43) if $\lambda = 2\lambda^*$ v is max. (find thru $\frac{dv}{d\lambda} = 0$) at a given ΔT_0 , or $\min \Delta T_0$ is min required for a given undercooling.

- If growth occurs under the optimum conditions the spacing (λ_0) and growth rate (v_0) will be $\lambda_0 = 2\lambda^*$, $v_0 = k_2 D \Delta T_0 / 4\lambda^*$ (why not $4\lambda^*$?)

$$(4.44) \quad (4.39) \rightarrow \Delta T_0 \propto \frac{1}{\lambda^*}$$

$$(4.45)$$

$$v_0 \lambda_0^2 = k_3 \text{ (const.) and } \frac{v_0}{(\Delta T_0)^2} = k_4 \text{ (const.)}$$

) exptly observed

- The total undercooling at the eutectic front (ΔT_0) has two components

$$(4.46) \quad \Delta T_0 = \Delta T_r + \Delta T_D. (+\Delta T_r) \text{ to move the atom across the interface, negligible for high}$$

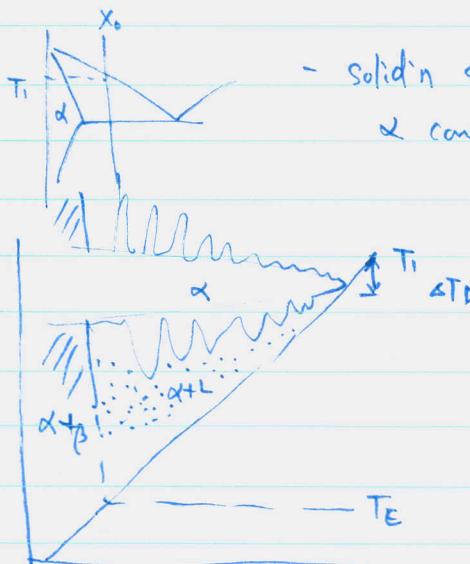
undercooling required to overcome the interfacial curvature \Rightarrow to have a suff. mobility interface

composition diff. to drive diffusion.

- Theoretically ΔT_D varies from α tip to β tip. \therefore diff. composition values
~~Since the interface is isothermal ($\Delta T_0 \text{ const}$)~~
~~the variation of T_0 causes ΔT_r to change correspondingly.~~
 \rightarrow i.e., the interface curvature change across the interface.

- Interface instability w/ planar interface: caused by impurities
 - Changing direction., fanning out to.
 \hookrightarrow can be stabilized by a high temp. grad. (DS).

3. Off-Eutectic Alloys.



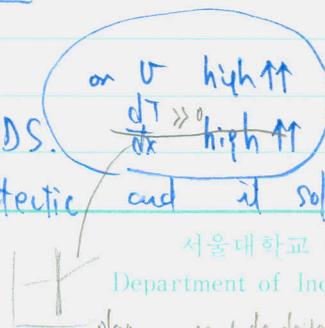
- Solid'n starts at T_i , forming α (primary dendrites)
 $\&$ contains less B \rightarrow rejecting into liquid & make $L \rightarrow T_E$

- w/ less solid-state diffusion, the centers of the dendrites have less solute than the outer layer.
 \rightarrow results in coring in the final struc.

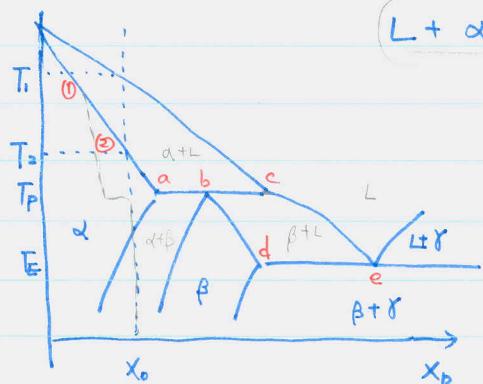
- The eutectic is lamellae as two-phase mixture or divorced eutectic: isolated islands of minor phase when vol. fractn of one phase is very small.

Fig. 4.37

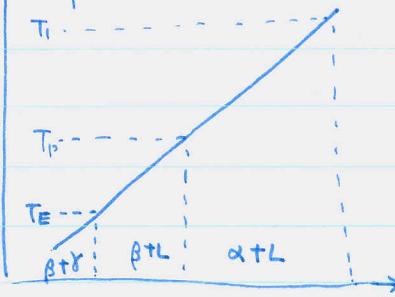
- In DS. $\frac{dT}{dx} \gg 0$ high $\uparrow\uparrow$
 eutectic and it solidifies 100% eutectic (overall comp. X_0)



4. Peritectic Solid'n.



'a' & 'c' make 'b' at T_P

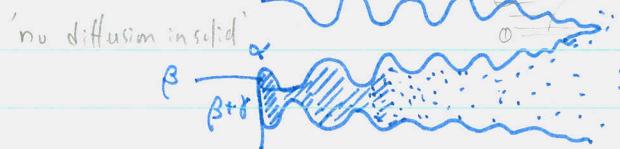


1) $\alpha : \sim kx_0 \sim T_L$

2) α grow with layer
of comps along solidus

(①-②) limited diff. in solid

3) If diffusion in dendrites
is slow, the liquid will
be at c comp.



4) Further cooling

$\alpha + L \rightarrow \beta$ layer (along b-d)



5) The remaining liquid, if there's no diffusion
in the solid, will reach e and produce $\beta + \gamma$

Directionally

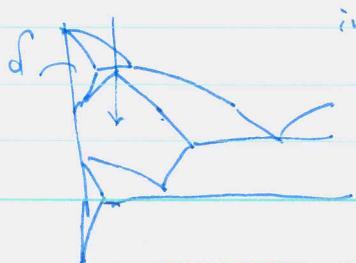
- If alloy x_0 were DSed at $(T_L'/v)t$, tip temp of dendrites fall from T_L to T_2 . & last liquid temp $\rightarrow T_2$

- Planar-front can be obtained for alloys beyond 'a' if T_L'/v $\uparrow\uparrow$ high.
alloys bet'n a & b - eutectic like $\alpha + \beta$ called composite.

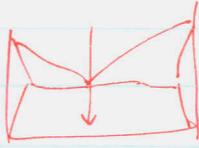
" b & d - β single phase.
beyond d - $\beta + \gamma$

- Fe-C. due to high diffusivity of C.

in peritectic rxn primary δ dendrites converts
into γ stable form.



1. ① x. β. L 의 free T diagram 은 (T_E , $T_F - \Delta T$, $T_E + \Delta T$ 이 관한) 2례시
 (G vs. Comp).



ⓐ ΔG 은 expression (가, 부활수로 표시하라) 2례시에 해당 quantity
 $\frac{2}{3}$ 표시하라

ⓑ lamellar 가 최대 속도가 되는 λ 를 구하라!